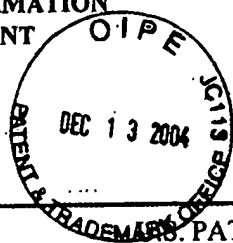


FORM PTO - 1449

SUPPLEMENTAL INFORMATION  
DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-23DVC2

APPLICANT(S): Fitzgerald

SERIAL NO.: 10/022,689

FILING DATE: December 17, 2001

GROUP: 2813

## PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>RL</i>	A121	4,969,031	11/06/1990	Kobayashi <i>et al.</i>			
<i>RL</i>	A122	5,240,876	08/31/1993	Gaul <i>et al.</i>			
<i>RL</i>	A123	5,548,128	08/20/1996	Soref <i>et al.</i>			
<i>RL</i>	A124	5,572,043	11/05/1996	Shimizu <i>et al.</i>			
<i>RL</i>	A125	5,607,876	03/04/1997	Biegelsen <i>et al.</i>			
<i>RL</i>	A126	6,352,909	03/05/2002	Usenko			05/26/2000
<i>RL</i>	A127	6,372,593	04/16/2002	Hattori <i>et al.</i>			07/19/2000
<i>RL</i>	A128	6,489,639	12/03/2002	Hoke <i>et al.</i>			05/24/2000
<i>RL</i>	A129	6,524,935	02/25/2003	Canaperi <i>et al.</i>			09/29/2000
<i>RL</i>	A130	6,646,322	11/11/2003	Fitzgerald			07/16/2001
<i>RL</i>	A131	6,677,192	01/13/2004	Fitzgerald			07/16/2001
<i>RL</i>	A132	6,703,688	03/09/2004	Fitzgerald			07/16/2001
<i>RL</i>	A133	6,750,130	06/15/2004	Fitzgerald			01/07/2001

## FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>RL</i>	B40	61-141116	06/28/1986	JP					Y (abstract only)
<i>RL</i>	B41	2-210816	08/22/1990	JP					Y (abstract only)
<i>RL</i>	B42	3-036717	02/18/1991	JP					Y

## OTHER ART, JOURNAL ARTICLES

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
<i>RL</i>	C95	Godbey <i>et al.</i> , (1990) "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained $\text{Si}_{0.7}\text{Ge}_{0.3}$ Layer as an Etch Stop," <i>Journal of the Electrical Society</i> , Vol. 137, No. 10 (October 1990) pp. 3219-3223.							
<i>RL</i>	C96	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in $(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{In}_{0.5}\text{P}$ heterostructures," <i>Journal of Applied Physics</i> , Vol. 91, No. 8 (2002), pp. 4891-4899.							

EXAMINER

*Wesley Schley*

DATE CONSIDERED

*3/3/05*

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[illegible][illegible]

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
	C97	Halsall <i>et al.</i> , "Electron diffraction and Raman studies of the effect of substrate misorientation on ordering in the AlGaInP system," <u>Journal of Applied Physics</u> , Vol. 85, No. 1 (1999), pp. 199-202.
	C98	Hsu <i>et al.</i> , "Surface morphology of related Ge <sub>x</sub> Si <sub>1-x</sub> films," <u>Appl. Phys. Lett.</u> , Vol. 61, No. 11 (1992), pp. 1293-1295
	C99	Huang <i>et al.</i> , (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", <u>2001 Symposium on VLSI Technology, Digest of Technical Papers</u> , pages 57-58
	C100	Langdo <i>et al.</i> , (2002) "Preparation of Novel SiGe-free Strained Si on Insulator Substrates" <u>IEEE International SOI Conference</u> , pages 211-212 (XP002263057)

**DATE CONSIDERED**

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